

**OBJECTION TO THE CLAIMS**

Claims 3-5, 7 and 8 are objected to for minor informalities. It is respectfully submitted that the enclosed amendment to those claims overcomes the alleged informalities. Accordingly, it is respectfully requested that the objection to the claims be withdrawn.

**IN THE SPECIFICATION**

The paragraph beginning on page 2, line 7 has been amended to read as follows:

a1 --Further, for higher probability of carrier injection, high voltage must be applied to the control gate electrode 205 for raising the potential bias between the floating gate and the drain, in order to electrically pull hot electrons toward the floating gate electrode 203.--

The paragraph beginning on page 74, line 7 has been amended to read as follows:

a2 --First, referring to FIG. 27A, a protective oxide film 21 made of silicon oxide is formed on the main surface of the semiconductor substrate 11, for example, made of silicon (Si), to protect the surface of the semiconductor substrate 11, by the thermal oxidation method, CVD method or other techniques. Subsequently, boron (B) ions are injected into the semiconductor substrate 11, which is the p-type impurity for controlling the threshold voltage, at an injection energy of about 30keV and a dose of  $5.0 \times 10^{12}/\text{cm}^2$  -  $1.0 \times 10^{13}/\text{cm}^2$ .--